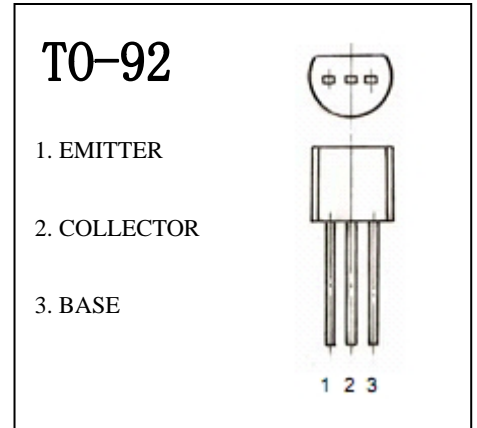


# 深圳市晶泰源电子有限公司

2SC2240 TRANSISTOR(NPN)

MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	120	V
VCEO	Collector-Emitter Voltage	120	V
VEBO	Emitter-Base Voltage	5	V
IC	Collector Current	0.1	A
PC	Collector Power Dissipation	300	mW
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55~150	°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	120			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	120			V
Emitter-base breakdown voltage	V(BR)EBO	IC=100uA, IC=0	5			V
Collector cut-off current	ICBO	VCB=120V, IE=0			0.1	μA
Emitter cut-off current	IEBO	VEB=5V, IC=0			0.1	μA
DC current gain	HFE	Vce=6V, Ic=2mA	200		700	
Collector-emitter saturation voltage	VCE(sat)	IC=10mA, IB=1mA			0.3	V
Base-emitter voltage	VBE	VCE=6V, IC=2mA		0.65		V
Transition frequency	fT	VCE=6V, IC=1mA		100		MHz
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz		4.0		pF